

Harri Lipsanen

List of Publications by Year in descending order

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405
papers

8,264
citations

61984

43
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74163

75
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408
all docs

408
docs citations

408
times ranked

9549
citing authors

#	ARTICLE	IF	CITATIONS
1	Nonlinear Optics with 2D Layered Materials. <i>Advanced Materials</i> , 2018, 30, e1705963.	21.0	485
2	Production and processing of graphene and related materials. <i>2D Materials</i> , 2020, 7, 022001.	4.4	333
3	Polarization and Thickness Dependent Absorption Properties of Black Phosphorus: New Saturable Absorber for Ultrafast Pulse Generation. <i>Scientific Reports</i> , 2015, 5, 15899.	3.3	268
4	Ultra-strong nonlinear optical processes and trigonal warping in MoS ₂ layers. <i>Nature Communications</i> , 2017, 8, 893.	12.8	177
5	Luminescence from excited states in strain-induced In _x Ga _{1-x} As quantum dots. <i>Physical Review B</i> , 1995, 51, 13868-13871.	3.2	174
6	Aluminum oxide from trimethylaluminum and water by atomic layer deposition: The temperature dependence of residual stress, elastic modulus, hardness and adhesion. <i>Thin Solid Films</i> , 2014, 552, 124-135.	1.8	155
7	Crystal-structure-dependent photoluminescence from InP nanowires. <i>Nanotechnology</i> , 2006, 17, 1580-1583.	2.6	152
8	A single-pixel wireless contact lens display. <i>Journal of Micromechanics and Microengineering</i> , 2011, 21, 125014.	2.6	121
9	Rapid visualization of grain boundaries in monolayer MoS ₂ by multiphoton microscopy. <i>Nature Communications</i> , 2017, 8, 15714.	12.8	120
10	Carrier relaxation dynamics in quantum dots: Scattering mechanisms and state-filling effects. <i>Physical Review B</i> , 1997, 55, 4473-4476.	3.2	119
11	Dispersion engineering of photonic crystal waveguides with ring-shaped holes. <i>Optics Express</i> , 2007, 15, 8323.	3.4	112
12	Properties of AlN grown by plasma enhanced atomic layer deposition. <i>Applied Surface Science</i> , 2011, 257, 7827-7830.	6.1	112
13	Ultra-high on-chip optical gain in erbium-based hybrid slot waveguides. <i>Nature Communications</i> , 2019, 10, 432.	12.8	100
14	Zeeman Effect in Parabolic Quantum Dots. <i>Physical Review Letters</i> , 1996, 77, 342-345.	7.8	99
15	Investigation of Second- and Third-Harmonic Generation in Few-Layer Gallium Selenide by Multiphoton Microscopy. <i>Scientific Reports</i> , 2015, 5, 10334.	3.3	98
16	A MoSe ₂ /WSe ₂ Heterojunction-Based Photodetector at Telecommunication Wavelengths. <i>Advanced Functional Materials</i> , 2018, 28, 1804388.	14.9	95
17	Selective growth of InGaAs on nanoscale InP islands. <i>Applied Physics Letters</i> , 1994, 65, 1662-1664.	3.3	93
18	Optical harmonic generation in monolayer group-VI transition metal dichalcogenides. <i>Physical Review B</i> , 2018, 98, .	3.2	92

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19	Catalyst-free growth of In(As)P nanowires on silicon. Applied Physics Letters, 2006, 89, 063119.	3.3	91
20	Tunable Graphene-GaSe Dual Heterojunction Device. Advanced Materials, 2016, 28, 1845-1852.	21.0	90
21	Strain-induced quantum dots by self-organized stressors. Applied Physics Letters, 1995, 66, 2364-2366.	3.3	88
22	Black phosphorus polycarbonate polymer composite for pulsed fibre lasers. Applied Materials Today, 2016, 4, 17-23.	4.3	87
23	Observation of defect complexes containing Ga vacancies in GaAsN. Applied Physics Letters, 2003, 82, 40-42.	3.3	84
24	High photoresponsivity and broadband photodetection with a band-engineered WSe ₂ /SnSe ₂ heterostructure. Nanoscale, 2019, 11, 3240-3247.	5.6	84
25	Rapid Large-Area Multiphoton Microscopy for Characterization of Graphene. ACS Nano, 2013, 7, 8441-8446.	14.6	81
26	Direct observation of confined acoustic phonon polarization branches in free-standing semiconductor nanowires. Nature Communications, 2016, 7, 13400.	12.8	71
27	Self-organized InP islands on (100) GaAs by metalorganic vapor phase epitaxy. Applied Physics Letters, 1995, 67, 3768-3770.	3.3	70
28	High Quality GaAs Nanowires Grown on Glass Substrates. Nano Letters, 2012, 12, 1912-1918.	9.1	70
29	Rapid and Large-Area Characterization of Exfoliated Black Phosphorus Using Third-Harmonic Generation Microscopy. Journal of Physical Chemistry Letters, 2017, 8, 1343-1350.	4.6	68
30	Temperature dependence of carrier relaxation in strain-induced quantum dots. Physical Review B, 1998, 58, R15993-R15996.	3.2	66
31	Thermal and plasma enhanced atomic layer deposition of SiO ₂ using commercial silicon precursors. Thin Solid Films, 2014, 558, 93-98.	1.8	66
32	Second-Harmonic Generation Imaging of Semiconductor Nanowires with Focused Vector Beams. Nano Letters, 2015, 15, 1564-1569.	9.1	66
33	Self-organized InAs islands on (100) InP by metalorganic vapor-phase epitaxy. Surface Science, 1997, 376, 60-68.	1.9	65
34	Review Article: Recommended reading list of early publications on atomic layer deposition—Outcome of the “Virtual Project on the History of ALD”, Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	2.1	65
35	Second and third harmonic generation in few-layer gallium telluride characterized by multiphoton microscopy. Applied Physics Letters, 2016, 108, .	3.3	58
36	Graphene-enhanced Raman imaging of TiO ₂ nanoparticles. Nanotechnology, 2012, 23, 465703.	2.6	56

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37	High nitrogen composition GaAsN by atmospheric pressure metalorganic vapor-phase epitaxy. <i>Journal of Crystal Growth</i> , 2000, 221, 456-460.	1.5	53
38	Nanowire network-based multifunctional all-optical logic gates. <i>Science Advances</i> , 2018, 4, eaar7954.	10.3	51
39	Superhydrophobic Antireflection Coating on Glass Using Grass-like Alumina and Fluoropolymer. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 49957-49962.	8.0	51
40	Noncovalent attachment of pyro-pheophorbidea to a carbon nanotube. <i>Chemical Communications</i> , 2007, , 519-521.	4.1	50
41	Solubility of Boron, Carbon, and Nitrogen in Transition Metals: Getting Insight into Trends from First-Principles Calculations. <i>Journal of Physical Chemistry Letters</i> , 2015, 6, 3263-3268.	4.6	50
42	Single-photon sources with quantum dots in III-V nanowires. <i>Nanophotonics</i> , 2019, 8, 747-769.	6.0	47
43	Photovoltaic properties of GaAsP core-shell nanowires on Si(001) substrate. <i>Nanotechnology</i> , 2012, 23, 265402.	2.6	45
44	Doping and carrier transport in Ga _{1-3x} In _{3x} N _x As _{1-x} alloys. <i>Physical Review B</i> , 2001, 64, .	3.2	43
45	Enhanced luminescence from catalyst-free grown InP nanowires. <i>Applied Physics Letters</i> , 2007, 90, 033101.	3.3	43
46	GaAs surface passivation by plasma-enhanced atomic-layer-deposited aluminum nitride. <i>Applied Surface Science</i> , 2010, 256, 7434-7437.	6.1	43
47	Crystal quality of two-dimensional gallium telluride and gallium selenide using Raman fingerprint. <i>AIP Advances</i> , 2017, 7, .	1.3	43
48	Synthesis of ZnO tetrapods for flexible and transparent UV sensors. <i>Nanotechnology</i> , 2012, 23, 095502.	2.6	40
49	Control of the morphology of InGaN/GaN quantum wells grown by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2007, 300, 324-329.	1.5	38
50	Mechanistic investigation of ZnO nanowire growth. <i>Applied Physics Letters</i> , 2009, 95, 183114.	3.3	38
51	Aluminum oxide/titanium dioxide nanolaminates grown by atomic layer deposition: Growth and mechanical properties. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2017, 35, .	2.1	38
52	Effect of substrate orientation on the catalyst-free growth of InP nanowires. <i>Nanotechnology</i> , 2007, 18, 155301.	2.6	37
53	Self-Assembled Porphyrins on Modified Zinc Oxide Nanorods: Development of Model Systems for Inorganic/Organic Semiconductor Interface Studies. <i>Journal of Physical Chemistry C</i> , 2012, 116, 2336-2343.	3.1	37
54	Synchrotron radiation x-ray topography and defect selective etching analysis of threading dislocations in GaN. <i>Journal of Applied Physics</i> , 2014, 116, 083504.	2.5	37

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55	Transformation of Self-Assembled InAs/InP Quantum Dots into Quantum Rings without Capping. Nano Letters, 2005, 5, 1541-1543.	9.1	36
56	Magneto-optical properties of strain-induced $\text{In}_x\text{Ga}_{1-x}\text{As}$ parabolic quantum dots. Physical Review B, 1998, 57, 9763-9769.	3.2	35
57	Capillary-driven self-assembly of microchips on oleophilic/oleophobic patterned surface using adhesive droplet in ambient air. Applied Physics Letters, 2011, 99, 034104.	3.3	34
58	Graphene actively Q-switched lasers. 2D Materials, 2017, 4, 025095.	4.4	34
59	Effects of few-particle interaction on the atomic-like levels of a single strain-induced quantum dot. Physical Review B, 2000, 62, 1592-1595.	3.2	33
60	Electrical measurement of internal quantum efficiency and extraction efficiency of III-N light-emitting diodes. Applied Physics Letters, 2012, 101, .	3.3	33
61	Enhanced optical properties of in situ passivated near-surface $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ quantum wells. Applied Physics Letters, 1996, 68, 2216-2218.	3.3	32
62	Photo-thermal chemical vapor deposition of graphene on copper. Carbon, 2013, 62, 43-50.	10.3	32
63	Influence of plasma chemistry on impurity incorporation in AlN prepared by plasma enhanced atomic layer deposition. Journal Physics D: Applied Physics, 2013, 46, 505502.	2.8	32
64	Corrosion protection of steel with multilayer coatings: Improving the sealing properties of physical vapor deposition CrN coatings with $\text{Al}_2\text{O}_3/\text{TiO}_2$ atomic layer deposition nanolaminates. Thin Solid Films, 2017, 627, 59-68.	1.8	32
65	Strong surface passivation of GaAs nanowires with ultrathin InP and GaP capping layers. Applied Physics Letters, 2014, 105, .	3.3	31
66	Review of fabrication methods of large-area transparent graphene electrodes for industry. Frontiers of Optoelectronics, 2020, 13, 91-113.	3.7	31
67	Interference effects in photoreflectance of epitaxial layers grown on semi-insulating substrates. Applied Physics Letters, 1993, 63, 2863-2865.	3.3	30
68	Growth of GaInAsSb using tertiarybutylarsine as arsenic source. Journal of Crystal Growth, 1994, 145, 492-497.	1.5	30
69	A physics-based model of gate-tunable metal-graphene contact resistance benchmarked against experimental data. 2D Materials, 2015, 2, 025006.	4.4	30
70	Young's Modulus of Wurtzite and Zinc Blende InP Nanowires. Nano Letters, 2017, 17, 3441-3446.	9.1	30
71	Trends in Carbon, Oxygen, and Nitrogen Core in the X-ray Absorption Spectroscopy of Carbon Nanomaterials: A Guide for the Perplexed. Journal of Physical Chemistry C, 2021, 125, 973-988.	3.1	30
72	Pauli-blocking imaging of single strain-induced semiconductor quantum dots. Applied Physics Letters, 1999, 74, 3200-3202.	3.3	29

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73	Protective capping and surface passivation of III-V nanowires by atomic layer deposition. AIP Advances, 2016, 6, .	1.3	29
74	Direct transfer of wafer-scale graphene films. 2D Materials, 2017, 4, 035004.	4.4	29
75	Demonstration of longitudinally polarized optical needles. Optics Express, 2018, 26, 27572.	3.4	29
76	Low Temperature Growth GaAs on Ge. Japanese Journal of Applied Physics, 2005, 44, 7777-7784.	1.5	28
77	X-ray reflectivity characterization of atomic layer deposition Al ₂ O ₃ /TiO ₂ nanolaminates with ultrathin bilayers. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2014, 32, .	2.1	28
78	Properties, applications and fabrication of photonic crystals with ring-shaped holes in silicon-on-insulator. Photonics and Nanostructures - Fundamentals and Applications, 2008, 6, 42-46.	2.0	27
79	Thermal conductivity of amorphous Al ₂ O ₃ /TiO ₂ nanolaminates deposited by atomic layer deposition. Nanotechnology, 2016, 27, 445704.	2.6	27
80	Atomic Layer Engineering of Er-Ion Distribution in Highly Doped Er:Al ₂ O ₃ for Photoluminescence Enhancement. ACS Photonics, 2016, 3, 2040-2048.	6.6	27
81	High performance complementary WS ₂ devices with hybrid Gr/Ni contacts. Nanoscale, 2020, 12, 21280-21290.	5.6	27
82	GaN quantum well structures for 1.55 μ m emission on GaAs by atmospheric pressure metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2002, 234, 631-636.	1.5	26
83	Impurity breakdown and terahertz luminescence in n-GaN epilayers under external electric field. Journal of Applied Physics, 2009, 106, 123523.	2.5	26
84	Nonlinear microscopy using cylindrical vector beams: Applications to three-dimensional imaging of nanostructures. Optics Express, 2017, 25, 12463.	3.4	26
85	High-speed InGaAsP/InP multiple-quantum-well laser. IEEE Photonics Technology Letters, 1992, 4, 673-675.	2.5	25
86	Room-temperature observation of impurity states in bulk GaAs by photoreflectance. Journal of Applied Physics, 1989, 65, 2556-2557.	2.5	24
87	Slow light propagation in photonic crystal waveguides with ring-shaped holes. Journal of Optics, 2007, 9, S415-S418.	1.5	24
88	Enhanced electroluminescence in 405nm InGaN/GaN LEDs by optimized electron blocking layer. Journal of Crystal Growth, 2008, 310, 5154-5157.	1.5	24
89	Surface-tension driven self-assembly of microchips on hydrophobic receptor sites with water using forced wetting. Applied Physics Letters, 2012, 101, 114105.	3.3	24
90	Impact of ALD grown passivation layers on silicon nitride based integrated optic devices for very-near-infrared wavelengths. Optics Express, 2014, 22, 5684.	3.4	24

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91	Direct Growth of Light-Emitting III-V Nanowires on Flexible Plastic Substrates. ACS Nano, 2020, 14, 7484-7491.	14.6	24
92	Passivation of GaAs surface by ultrathin epitaxial GaN layer. Journal of Crystal Growth, 2004, 272, 621-626.	1.5	23
93	Effect of growth conditions on electrical properties of Mg-doped p-GaN. Journal of Crystal Growth, 2007, 298, 811-814.	1.5	23
94	The effect of InGaN/GaN MQW hydrogen treatment and threading dislocation optimization on GaN LED efficiency. Journal of Crystal Growth, 2007, 298, 740-743.	1.5	23
95	Aluminum-Induced Photoluminescence Red Shifts in Core-Shell GaAs/Al _x Ga _{1-x} As Nanowires. Nano Letters, 2013, 13, 3581-3588.	9.1	23
96	Tailorable second-harmonic generation from an individual nanowire using spatially phase-shaped beams. Laser and Photonics Reviews, 2017, 11, 1600175.	8.7	23
97	Photoresponse of Graphene-Gated Graphene-GaSe Heterojunction Devices. ACS Applied Nano Materials, 2018, 1, 3895-3902.	5.0	23
98	Enhanced Tunneling in a Hybrid of Single-Walled Carbon Nanotubes and Graphene. ACS Nano, 2019, 13, 11522-11529.	14.6	23
99	Morphology optimization of MOCVD-grown GaN nucleation layers by the multistep technique. Journal of Crystal Growth, 2006, 292, 26-32.	1.5	22
100	Metal Contacts on InN: Proposal for Schottky Contact. Japanese Journal of Applied Physics, 2006, 45, 36-39.	1.5	22
101	High-quality crystallinity controlled ALD TiO ₂ for waveguiding applications. Optics Letters, 2013, 38, 3980.	3.3	22
102	Structural and chemical analysis of annealed plasma-enhanced atomic layer deposition aluminum nitride films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	2.1	22
103	Experimental investigation towards a periodically pumped single-photon source. Physical Review B, 2006, 74, .	3.2	21
104	Generation of terahertz radiation in ordered arrays of GaAs nanowires. Applied Physics Letters, 2015, 106, .	3.3	21
105	Growth of high-quality GaSb by metalorganic vapor phase epitaxy. Journal of Electronic Materials, 1995, 24, 1691-1696.	2.2	20
106	Atomic layer deposition of ytterbium oxide using -diketonate and ozone precursors. Applied Surface Science, 2009, 256, 847-851.	6.1	20
107	High-k GaAs metal insulator semiconductor capacitors passivated by ex-situ plasma-enhanced atomic layer deposited AlN for Fermi-level unpinning. Applied Physics Letters, 2012, 100, .	3.3	20
108	Large-area analysis of dislocations in ammonothermal GaN by synchrotron radiation X-ray topography. Applied Physics Express, 2014, 7, 091003.	2.4	20

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109	Erbium-doped hybrid waveguide amplifiers with net optical gain on a fully industrial 300 mm silicon nitride photonic platform. <i>Optics Express</i> , 2020, 28, 27919.	3.4	20
110	Ultra-Thin Silicon Nitride X-Ray Windows. <i>IEEE Transactions on Nuclear Science</i> , 2013, 60, 1311-1314.	2.0	19
111	Effect of growth temperature on the epitaxial growth of ZnO on GaN by ALD. <i>Journal of Crystal Growth</i> , 2014, 398, 18-22.	1.5	19
112	Atomic layer deposition of AlN from AlCl ₃ using NH ₃ and Ar/NH ₃ plasma. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2018, 36, .	2.1	19
113	Electron-Hole Correlation in Quantum Dots under a High Magnetic Field (up to 45 T). <i>Physical Review Letters</i> , 1999, 83, 4832-4835.	7.8	18
114	Self-assembled GaIn(N)As quantum dots: Enhanced luminescence at 1.3 μm. <i>Applied Physics Letters</i> , 2001, 79, 3932-3934.	3.3	18
115	Multistep method for threading dislocation density reduction in MOCVD grown GaN epilayers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006, 203, R76-R78.	1.8	18
116	Passivation of GaAs surface by atomic-layer-deposited titanium nitride. <i>Applied Surface Science</i> , 2008, 254, 5385-5389.	6.1	18
117	Surface-Tension-Driven Self-Alignment of Microchips on Black-Silicon-Based Hybrid Template in Ambient Air. <i>Journal of Microelectromechanical Systems</i> , 2013, 22, 739-746.	2.5	18
118	Effect of Surface Wear on Corrosion Protection of Steel by CrN Coatings Sealed with Atomic Layer Deposition. <i>ACS Omega</i> , 2018, 3, 1791-1800.	3.5	18
119	InAs-Nanowire-Based Broadband Ultrafast Optical Switch. <i>Journal of Physical Chemistry Letters</i> , 2019, 10, 4429-4436.	4.6	18
120	Applied electromagnetic optics simulations for nanophotonics. <i>Journal of Applied Physics</i> , 2021, 129, .	2.5	18
121	Photoreflectance study of photovoltage effects in GaAs diode structures. <i>Applied Physics Letters</i> , 1992, 60, 2110-2112.	3.3	17
122	Metalorganic vapor phase epitaxial growth of AlGaSb and AlGaAsSb using all-organometallic sources. <i>Journal of Crystal Growth</i> , 1996, 169, 417-423.	1.5	17
123	Red luminescence from strain-induced GaInP quantum dots. <i>Applied Physics Letters</i> , 1996, 69, 3393-3395.	3.3	17
124	Mechanical nanomanipulation of single strain-induced semiconductor quantum dots. <i>Applied Physics Letters</i> , 1999, 75, 358-360.	3.3	17
125	Low-height sharp edged patterns for capillary self-alignment assisted hybrid microassembly. <i>Journal of Micro-Bio Robotics</i> , 2014, 9, 1-10.	2.1	17
126	Aluminum Nitride Transition Layer for Power Electronics Applications Grown by Plasma-Enhanced Atomic Layer Deposition. <i>Materials</i> , 2019, 12, 406.	2.9	17

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127	Mechanical and optical properties of as-grown and thermally annealed titanium dioxide from titanium tetrachloride and water by atomic layer deposition. <i>Thin Solid Films</i> , 2021, 732, 138758.	1.8	17
128	Single-step chemical vapour deposition of anti-pyramid MoS ₂ /WS ₂ vertical heterostructures. <i>Nanoscale</i> , 2021, 13, 4537-4542.	5.6	17
129	Genetic algorithm using independent component analysis in x-ray reflectivity curve fitting of periodic layer structures. <i>Journal Physics D: Applied Physics</i> , 2007, 40, 6000-6004.	2.8	16
130	Nonlinear fitness "space" structure adaptation and principal component analysis in genetic algorithms: an application to x-ray reflectivity analysis. <i>Journal Physics D: Applied Physics</i> , 2007, 40, 215-218.	2.8	16
131	Nanowire encapsulation with polymer for electrical isolation and enhanced optical properties. <i>Nano Research</i> , 2017, 10, 2657-2666.	10.4	16
132	Influence of plasma parameters on the properties of ultrathin Al ₂ O ₃ films prepared by plasma enhanced atomic layer deposition below 100 Å°C for moisture barrier applications. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 125502.	1.5	16
133	Fabrication and photoluminescence of quantum dots induced by strain of self-organized stressors. <i>Solid-State Electronics</i> , 1996, 40, 601-604.	1.4	15
134	Void shape control in GaN re-grown on hexagonally patterned mask-less GaN. <i>Journal of Crystal Growth</i> , 2011, 315, 188-191.	1.5	15
135	Improved SERS Intensity from Silver-Coated Black Silicon by Tuning Surface Plasmons. <i>Advanced Materials Interfaces</i> , 2014, 1, 1300008.	3.7	15
136	Performance and Properties of Ultra-Thin Silicon Nitride X-ray Windows. <i>IEEE Transactions on Nuclear Science</i> , 2014, 61, 695-699.	2.0	15
137	Scaling of graphene field-effect transistors supported on hexagonal boron nitride: radio-frequency stability as a limiting factor. <i>Nanotechnology</i> , 2017, 28, 485203.	2.6	15
138	Ultrafast Relaxation Dynamics in Strain-Induced Quantum Dots. <i>Physica Status Solidi (B): Basic Research</i> , 1997, 204, 251-254.	1.5	14
139	Synchrotron X-ray topography study of defects in indium antimonide P-I-N structures grown by metal organic vapour phase epitaxy. <i>Journal of Materials Science: Materials in Electronics</i> , 2005, 16, 449-453.	2.2	14
140	Analysis of threading dislocations in void shape controlled GaN re-grown on hexagonally patterned mask-less GaN. <i>Journal of Crystal Growth</i> , 2012, 344, 59-64.	1.5	14
141	Broadband laser polarization control with aligned carbon nanotubes. <i>Nanoscale</i> , 2015, 7, 11199-11205.	5.6	14
142	All-Graphene Three-Terminal-Junction Field-Effect Devices as Rectifiers and Inverters. <i>ACS Nano</i> , 2015, 9, 5666-5674.	14.6	14
143	Slot waveguide ring resonators coated by an atomic layer deposited organic/inorganic nanolaminate. <i>Optics Express</i> , 2015, 23, 26940.	3.4	14
144	Spontaneous and stimulated emission in InAsSb-based LED heterostructures. <i>Infrared Physics and Technology</i> , 2017, 85, 246-250.	2.9	14

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145	All-parylene flexible wafer-scale graphene thin film transistor. <i>Applied Surface Science</i> , 2021, 551, 149410.	6.1	14
146	Multilayer MoTe ₂ Field-Effect Transistor at High Temperatures. <i>Advanced Materials Interfaces</i> , 2021, 8, 2100950.	3.7	14
147	MOVPE growth and characterization of InAlGaN films and InGaN/InAlGaN MQW structures. <i>Journal of Crystal Growth</i> , 2008, 310, 1777-1780.	1.5	13
148	InGaN-based 405 nm near-ultraviolet light emitting diodes on pillar patterned sapphire substrates. <i>CrystEngComm</i> , 2010, 12, 3152.	2.6	13
149	Growth temperature dependence of the electrical and structural properties of epitaxial graphene on SiC(0001). <i>Physica Status Solidi (B): Basic Research</i> , 2011, 248, 1908-1914.	1.5	13
150	Nonlinear behavior of three-terminal graphene junctions at room temperature. <i>Nanotechnology</i> , 2012, 23, 115201.	2.6	13
151	Ferromagnetic (Ga,Mn)As nanowires grown by Mn-assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2013, 113, .	2.5	13
152	Defect structure of a free standing GaN wafer grown by the ammonothermal method. <i>Journal of Crystal Growth</i> , 2014, 406, 72-77.	1.5	13
153	Wafer-scale self-organized InP nanopillars with controlled orientation for photovoltaic devices. <i>Nanotechnology</i> , 2015, 26, 415304.	2.6	13
154	Nanotribological, nanomechanical and interfacial characterization of atomic layer deposited TiO ₂ on a silicon substrate. <i>Wear</i> , 2015, 342-343, 270-278.	3.1	13
155	Comparison of absorption simulation in semiconductor nanowire and nanocone arrays with the Fourier modal method, the finite element method, and the finite-difference time-domain method. <i>Nano Express</i> , 2020, 1, 030034.	2.4	13
156	Comparison of epitaxial thin layer GaN and InP passivations on InGaAs [*] -GaAs near-surface quantum wells. <i>Applied Physics Letters</i> , 2006, 88, 221112.	3.3	12
157	Fitness function and nonunique solutions in x-ray reflectivity curve fitting: crosserror between surface roughness and mass density. <i>Journal Physics D: Applied Physics</i> , 2007, 40, 4259-4263.	2.8	12
158	Plasma etch characteristics of aluminum nitride mask layers grown by low-temperature plasma enhanced atomic layer deposition in SF ₆ based plasmas. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2012, 30, .	2.1	12
159	Stress distribution of GaN layer grown on micro-pillar patterned GaN templates. <i>Applied Physics Letters</i> , 2013, 103, .	3.3	12
160	Photo-induced electron transfer at nanostructured semiconductor-zinc porphyrin interface. <i>Chemical Physics Letters</i> , 2014, 592, 47-51.	2.6	12
161	Substitutionality of nitrogen atoms and formation of nitrogen complexes and point defects in GaPN alloys. <i>Journal Physics D: Applied Physics</i> , 2014, 47, 075106.	2.8	12
162	Pyrolytic carbon coated black silicon. <i>Scientific Reports</i> , 2016, 6, 25922.	3.3	12

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163	Active synchronization and modulation of fiber lasers with a graphene electro-optic modulator. Optics Letters, 2018, 43, 3497.	3.3	12
164	Identifying threading dislocation types in ammonothermally grown bulk GaN by confocal Raman 3-D imaging of volumetric stress distribution. Journal of Crystal Growth, 2018, 499, 47-54.	1.5	12
165	Structural and optical properties of GaInNAs/GaAs quantum structures. Journal of Physics Condensed Matter, 2004, 16, S3009-S3026.	1.8	11
166	GaAs Medipix2 hybrid pixel detector. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2008, 591, 174-177.	1.6	11
167	Influence of substrate temperature on the shape of GaAs nanowires grown by Au-assisted MOVPE. Journal of Crystal Growth, 2010, 312, 1676-1682.	1.5	11
168	Patterning of sapphire/GaN substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1509-1512.	0.8	11
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